Supplementary Information (SI) for Nanoscale Horizons.
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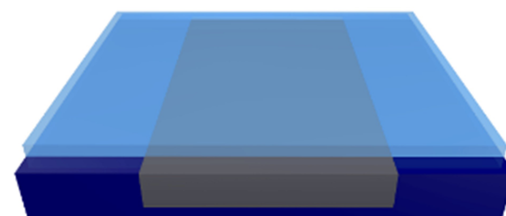
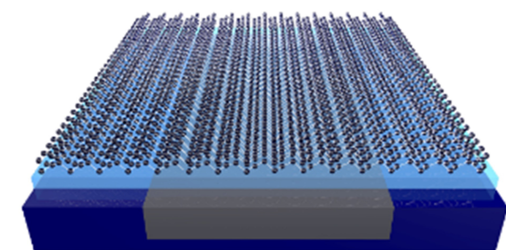
1. Buried gate formation

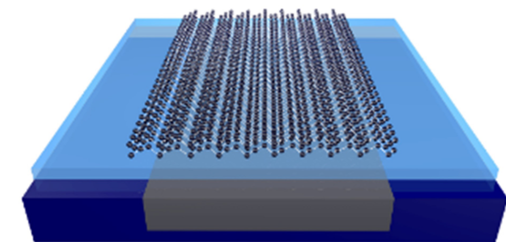
- SiO_2 trench formation
- Aluminum deposition
- Lift-off


2. Dielectric deposition

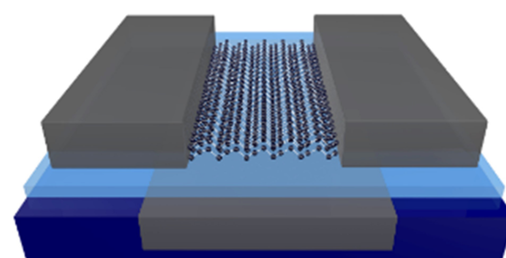
- Al_2O_3 12 nm deposition at 200 ℃


3. Channel deposition

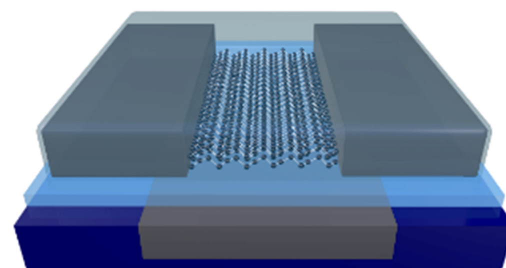
- TeO_x 3 nm deposition by sputtering
- Te deposition by ALD at 80 ℃


4. Channel patterning

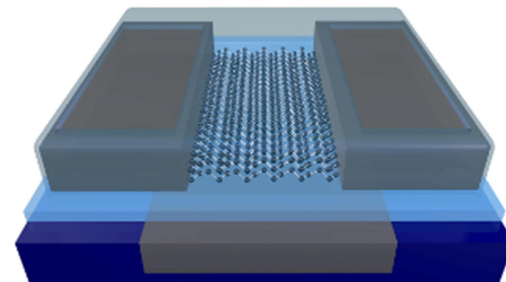
- Dry etching


5. Source/Drain formation

- Source/Drain electrode patterning
- Nickel deposition
- Lift-off


6. Passivation layer deposition

- Al_2O_3 10 nm deposition


7. Contact pad open

- Contact pad open patterning
- Wet etching